

## BAV19 THRU BAV21

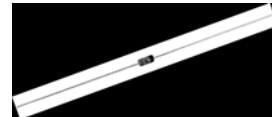
### TECHNICAL SPECIFICATIONS OF HIGH SPEED SWITCHING DIODES VOLTAGE RANGE - 100 to 200 Volts      CURRENT - 0.2 Ampere

#### FEATURES

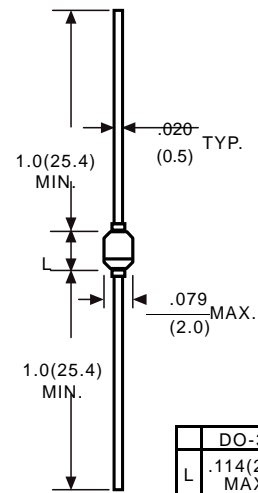
- \* Silicon epitaxial planar diodes
- \* Low power loss, high efficiency
- \* Low leakage
- \* Low forward voltage
- \* High current capability
- \* High reliability

#### MECHANICAL DATA

- \* Case: Glass sealed case
- \* Lead: Solder plated, solderable per MIL-STD-202E, Method 208 guaranteed
- \* Polarity: Color band denotes cathode end
- \* Mounting position: Any
- \* Weight: 0.13 grams Approx.



DO-34 / DO-35



Dimensions in inches and (millimeters)

**MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS**  
Ratings at 25°C ambient temperature unless otherwise specified.  
Single phase, half wave, 60 Hz, resistive or inductive load.  
For capacitive load, derate current by 20%.

	SYMBOL	BAV19	BAV20	BAV21	UNITS
Maximum Reverse Voltage	VR	100	150	200	V
Maximum Recurrent Peak Reverse Voltage	VRRM	120	200	250	V
Maximum Average Rectified Current	Io	200			mA
Peak Forward Surge Current, 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	1.0			A
Maximum Power Dissipation Tamb=25°C	Ptot	500			mW
Maximum Forward Voltage (@IF=100mA)	VF	1.0			V
Maximum Reverse Current (@VR=VR Max)	IR	0.1			µA
Maximum Reverse Recovery Time(Note 1)	trr	50			nS
Typical Junction Capacitance(Note 2)	CJ	1.5			pF
Typical Thermal Resistance	RθJA	357			°C/W
Operating and Storage Temperature Range	TJ,TSTG	-55 to +125			°C

Note: 1. Test Conditions: IF=IR=10mA, RL=100Ω, VR=6V to IRR=1mA, RL=100Ω  
2. Measured at 1MHz and VR=0  
3. Suffix "M" stands for "DO-34" package.(e.g.: BAV19M)

# RATING AND CHARACTERISTIC CURVES (BAV19 THRU BAV21)

FIG.1 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

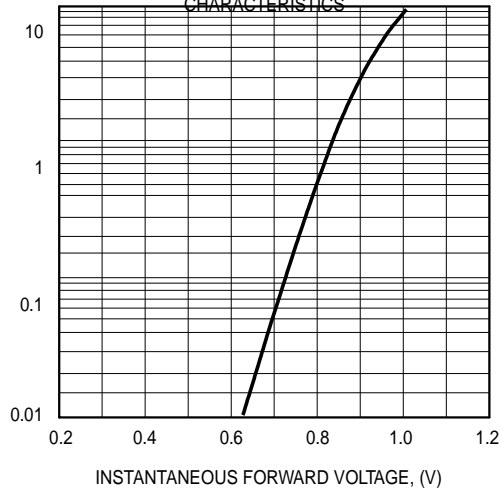


FIG.2 - TYPICAL REVERSE CHARACTERISTICS

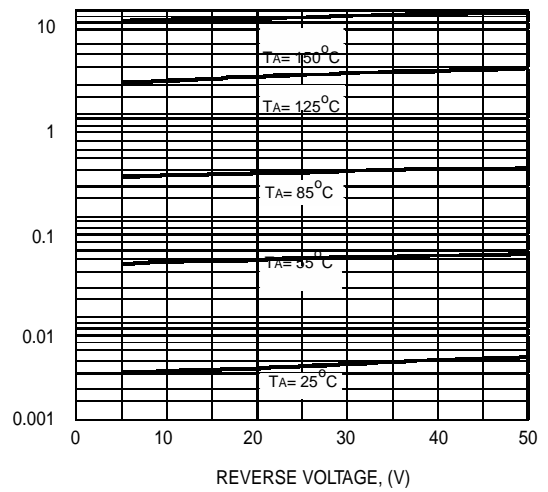


FIG.3 - TYPICAL JUNCTION CAPACITANCE

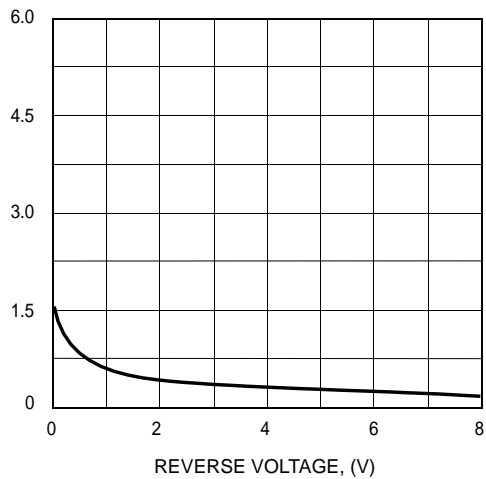


FIG.4 - RECTIFICATION EFFICIENCY MEASUREMENT CIRCUIT

